

# H5N5001FM

Silicon N Channel MOS FET  
High Speed Power Switching

**RENESAS**

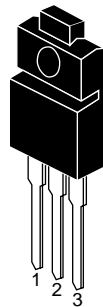
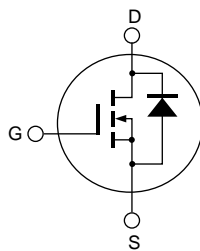
ADE-208-1380 (Z)  
1st. Edition  
Mar. 2001

## Features

- Low on-resistance :  $R_{DS(on)} = 1.1\Omega$  typ.
- Low leakage current :  $I_{DSS} = 1\mu A$  max (at  $V_{DS} = 500 V$ )
- High speed switching :  $t_f = 15ns$  typ (at  $V_{GS} = 10 V$ ,  $V_{DD} = 250 V$ ,  $I_D = 2.5 A$ )
- Low gate charge :  $Q_g = 15nC$  typ (at  $V_{DD} = 400 V$ ,  $V_{GS} = 10 V$ ,  $I_D = 5 A$ )
- Avalanche ratings

## Outline

TO-220FM



1. Gate
2. Drain
3. Source

## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	500	V
Gate to source voltage	$V_{GSS}$	±30	V
Drain current	$I_D$	5	A
Drain peak current	$I_{D(pulse)}$ <sup>Note1</sup>	20	A
Body-drain diode reverse drain current	$I_{DR}$	5	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}$ <sup>Note1</sup>	20	A
Avalanche current	$I_{AP}$ <sup>Note3</sup>	5	A
Channel dissipation	$P_{ch}$ <sup>Note2</sup>	30	W
Channel to case Thermal Impedance	$\theta_{ch-c}$	4.17	°C/W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Note: 1.  $PW \leq 10\mu s$ , duty cycle  $\leq 1\%$

2. Value at  $T_c = 25^\circ C$

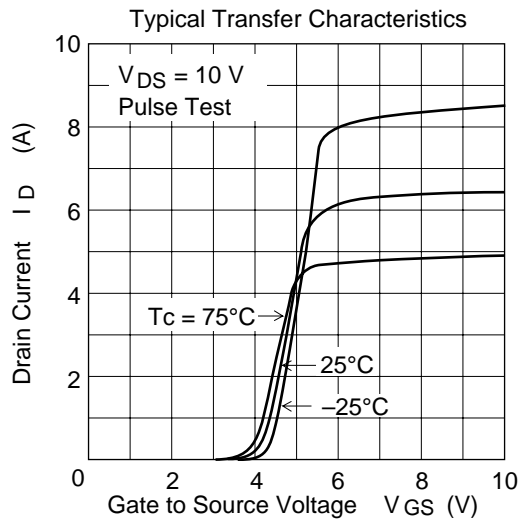
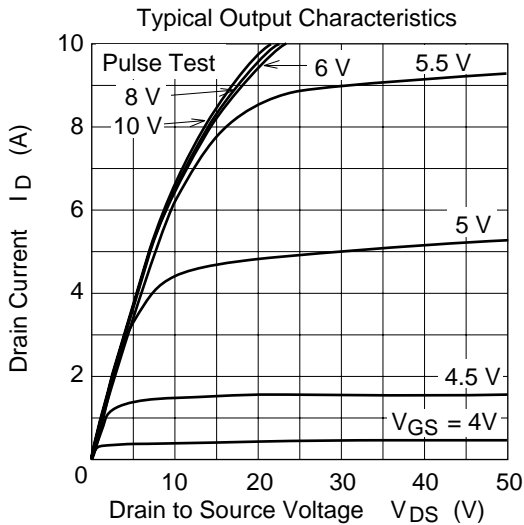
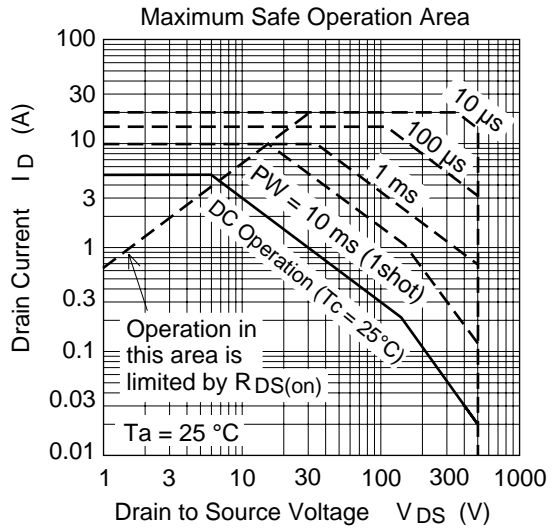
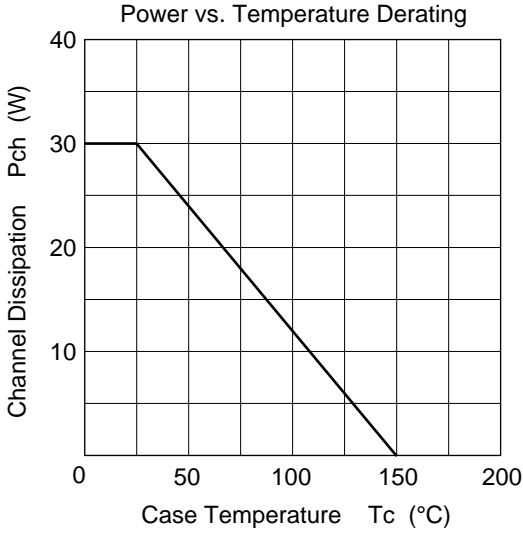
3.  $T_{ch} \leq 150^\circ C$

## Electrical Characteristics (Ta = 25°C)

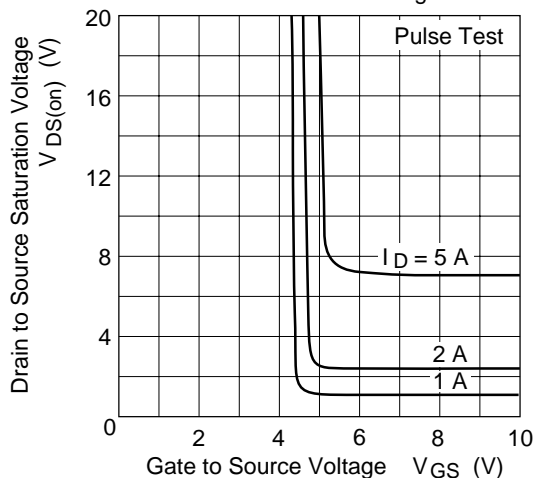
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	$I_D = 10\text{mA}$ , $V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 0.1$	$\mu\text{A}$	$V_{GS} = \pm 30\text{V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 500\text{V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.0	V	$I_D = 1\text{mA}$ , $V_{DS} = 10\text{V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	1.1	1.5	$\Omega$	$I_D = 2.5\text{A}$ , $V_{GS} = 10\text{V}$ <sup>Note4</sup>
Forward transfer admittance	$ y_{fs} $	3.0	4.5	—	S	$I_D = 2.5\text{A}$ , $V_{DS} = 10\text{V}$ <sup>Note4</sup>
Input capacitance	$C_{iss}$	—	580	—	pF	$V_{DS} = 25\text{V}$
Output capacitance	$C_{oss}$	—	70	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	13	—	pF	$f = 1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$I_D = 2.5\text{A}$
Rise time	$t_r$	—	15	—	ns	$V_{GS} = 10\text{V}$
Turn-off delay time	$t_{d(off)}$	—	65	—	ns	$R_L = 100\Omega$
Fall time	$t_f$	—	15	—	ns	$R_g = 10\Omega$
Total gate charge	$Q_g$	—	15	—	nC	$V_{DD} = 400\text{V}$
Gate to source charge	$Q_{gs}$	—	3	—	nC	$V_{GS} = 10\text{V}$
Gate to drain charge	$Q_{gd}$	—	8	—	nC	$I_D = 5\text{A}$
Body–drain diode forward voltage	$V_{DF}$	—	0.85	1.3	V	$I_F = 5\text{A}$ , $V_{GS} = 0$
Body–drain diode reverse recovery time	$t_{rr}$	—	400	—	ns	$I_F = 5\text{A}$ , $V_{GS} = 0$ $diF/dt = 100\text{A}/\mu\text{s}$
Body–drain diode reverse recovery charge	$Q_{rr}$	—	1.5	—	$\mu\text{C}$	

Note: 4. Pulse test

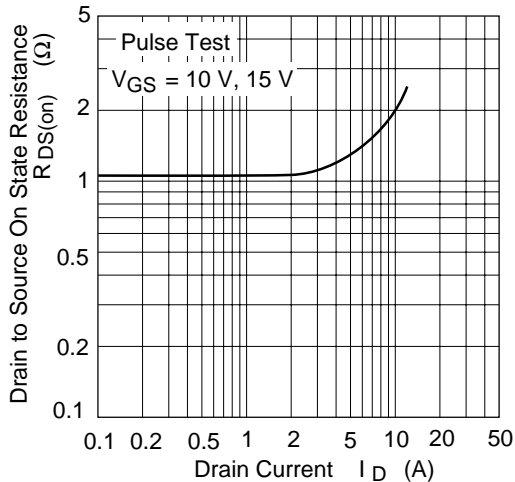
## Main Characteristics



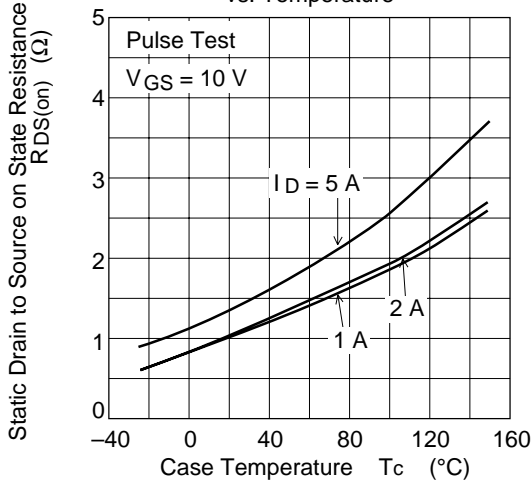
Drain to Source Saturation Voltage vs. Gate to Source Voltage



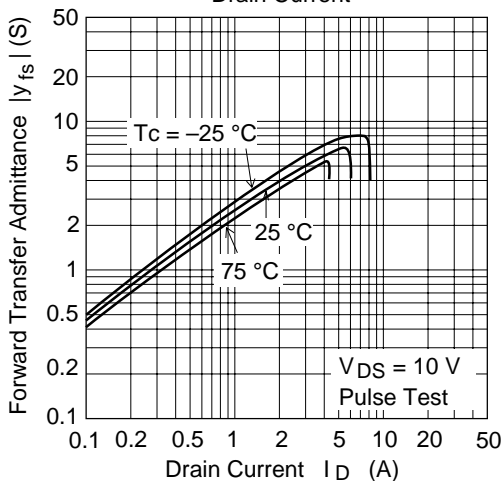
Static Drain to Source on State Resistance vs. Drain Current



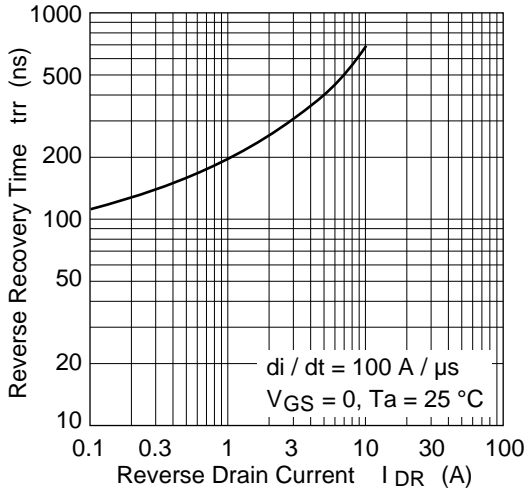
Static Drain to Source on State Resistance vs. Temperature



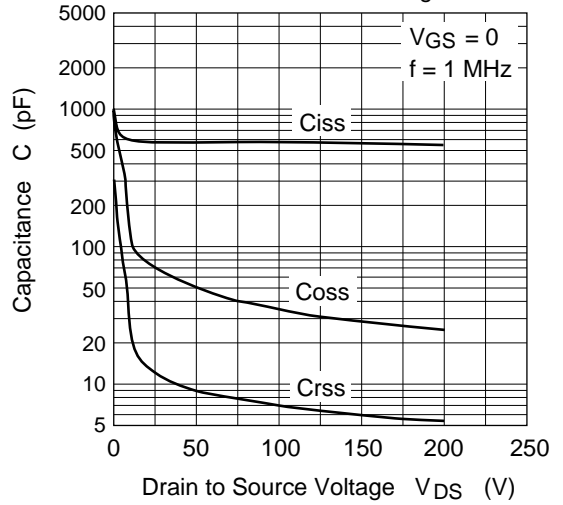
Forward Transfer Admittance vs. Drain Current



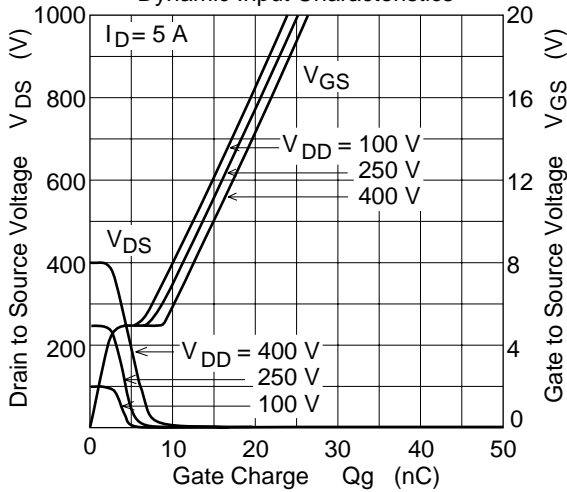
Body-Drain Diode Reverse Recovery Time



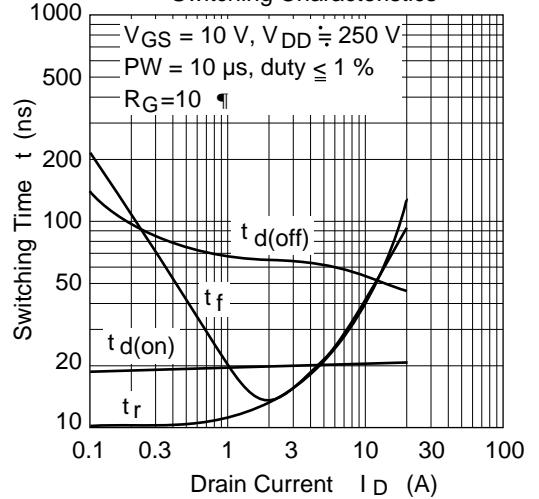
Typical Capacitance vs. Drain to Source Voltage

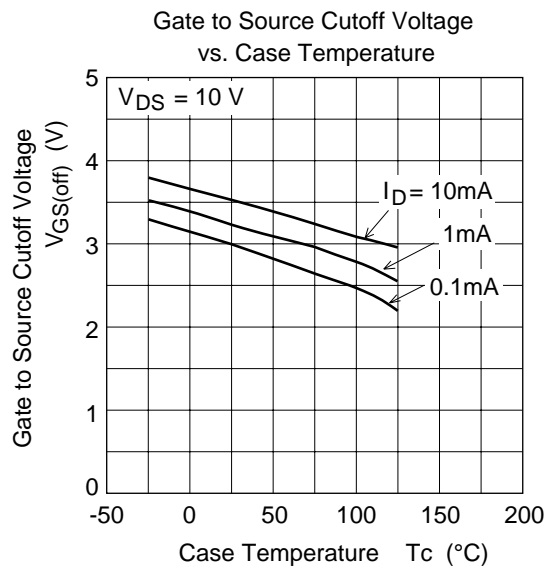
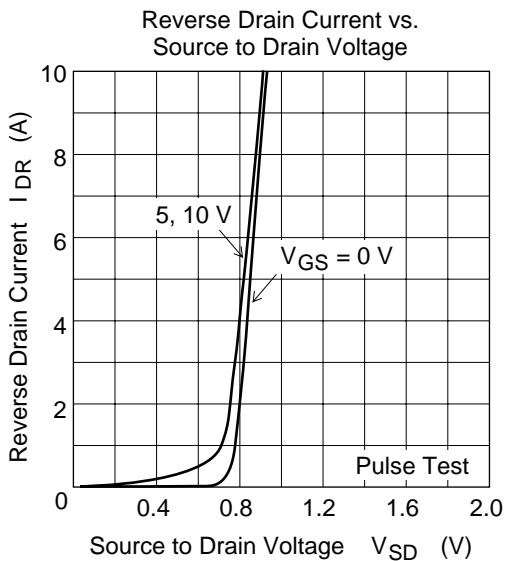


Dynamic Input Characteristics

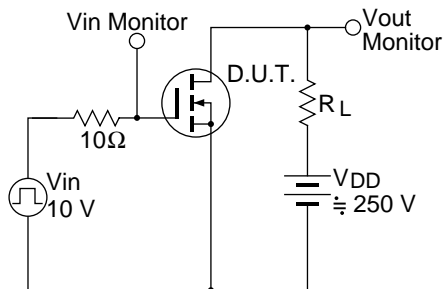


Switching Characteristics

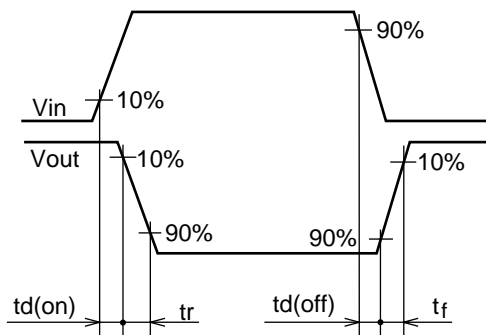




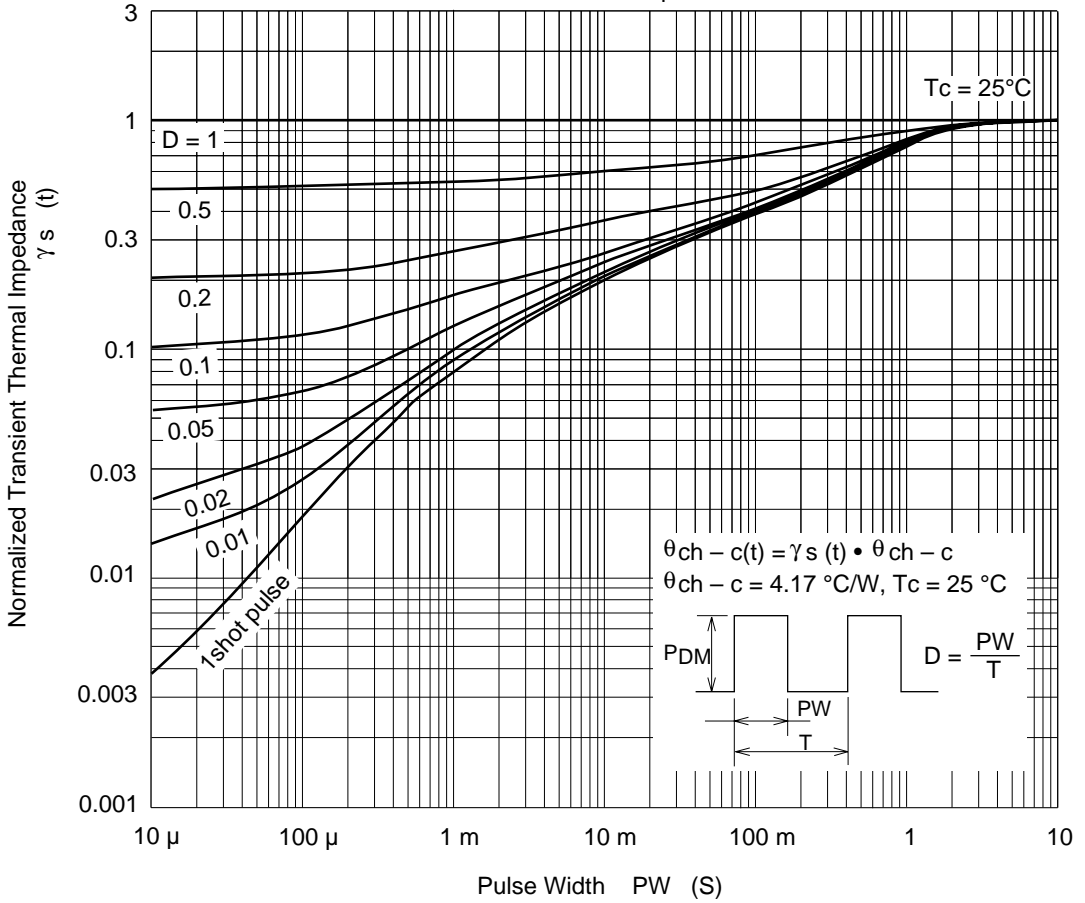
Switching Time Test Circuit



Waveform

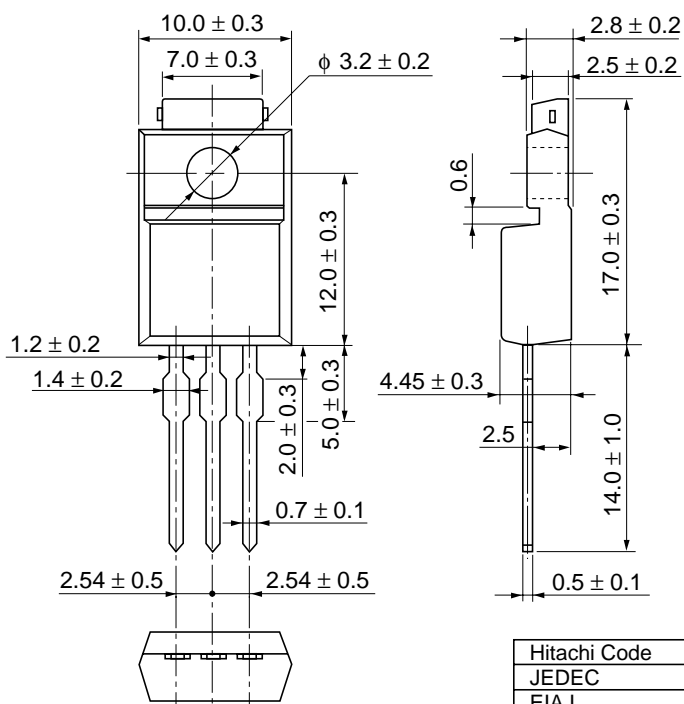


Normalized Transient Thermal Impedance vs. Pulse Width

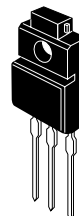




Package Dimensions



As of January, 2001  
Unit: mm



Hitachi Code	TO-220FM
JEDEC	—
EIAJ	Conforms
Mass (reference value)	1.8 g

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# HITACHI

## Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL       NorthAmerica       : <http://semiconductor.hitachi.com/>  
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## For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic Components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 585160

Hitachi Asia Ltd.  
Hitachi Tower  
16 Collyer Quay #20-00,  
Singapore 049318  
Tel : <65>-538-6533/538-8577  
Fax : <65>-538-6933/538-3877  
URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.  
(Taipei Branch Office)  
4/F, No. 167, Tun Hwa North Road,  
Hung-Kuo Building,  
Taipei (105), Taiwan  
Tel : <886>-(2)-2718-3666  
Fax : <886>-(2)-2718-8180  
Telex : 23222 HAS-TP  
URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.  
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Hong Kong  
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